

131,072 WORD $\times$ 8 Bit CMOS Static RAM

FEATURES

- Fast Access Time: 55, 70, 85, 100ns (max.)
- Low Power Dissipation
 - Standby (CMOS): $10\mu\text{W}$ (typ.) L-Version
 - $5\mu\text{W}$ (typ.) LL-Version
 - Operating : 35mA (typ.)
- Single $5\text{V} \pm 10\%$ Power Supply
- TTL compatible inputs and outputs
- Fully Static Operation
 - No clock or refresh required
- Three State Output
- Battery Back-up Operation
 - 2V (min.) Data Retention
- Standard Pin Configuration
 - KM681000BLP/BLP-L : 32 pin-DIP (mail)
 - KM681000BLG/BLG-L : 32 pin-SOP (525 mil)
 - KM681000BLT/BLT-L : 32 pin-TSOP (Standard Type)
 - KM681000BLR/BLR-L : 32 pin-TSOP (Reverse Type)

GENERAL DESCRIPTION

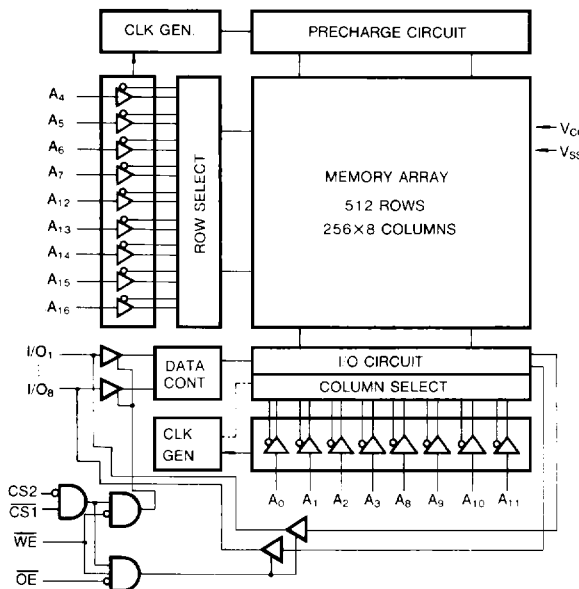
The KM681000BL/BL-L is a 1,048,576-bit high-speed Static Random Access Memory organized as 131,072 words by 8 bits.

The device is fabricated using Samsung's advanced CMOS process.

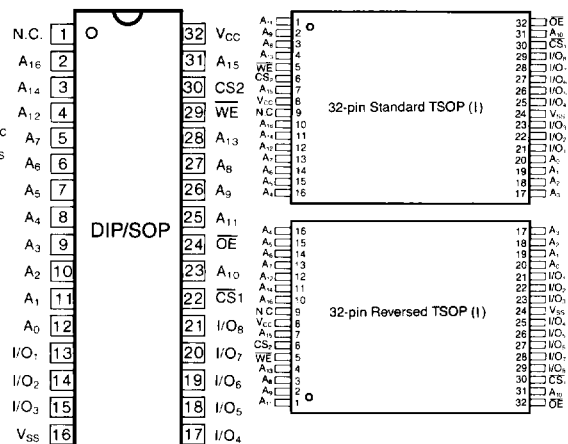
The KM681000BL/BL-L has an output enable input for precise control of the data outputs. It also has chip enable inputs for the minimum current power down mode.

The KM681000BL/BL-L has been designed for high speed and low power applications. It is particularly well suited for battery back-up nonvolatile memory application.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION (Top Views)



Pin Name	Pin Function
A ₀ -A ₁₆	Address Inputs
WE	Write Enable Input
CS ₁ , CS ₂	Chip Sleet Inputs
OE	Output Enable Input
I/O ₁ ~ I/O ₈	Data Inputs/Outputs
V _{CC}	Power (+5V)
V _{SS}	Ground
N.C.	No Connection